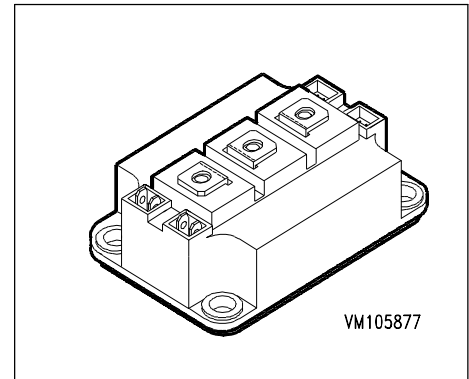


IGBT Power Module

- Single switch with chopper diode at collector
- Chopper diode like diode of BSM300GA120DN2
- Package with insulated metal base plate



Type	V_{CE}	I_C	Package	Ordering Code
BSM 200 GAL 120 DN2	1200V	290A	HB 200GAL	C67070-A2301-A70

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage	V_{CGR}	1200	
$R_{GE} = 20 \text{ k}\Omega$			
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I_C	290	A
$T_C = 25 \text{ }^\circ\text{C}$			
$T_C = 80 \text{ }^\circ\text{C}$		200	
Pulsed collector current, $t_p = 1 \text{ ms}$	I_{Cpuls}	580	
$T_C = 25 \text{ }^\circ\text{C}$			
$T_C = 80 \text{ }^\circ\text{C}$		400	
Power dissipation per IGBT	P_{tot}	1400	W
$T_C = 25 \text{ }^\circ\text{C}$			
Chip temperature	T_j	+ 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 ... + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.09	K/W
Diode thermal resistance, chip case	R_{thJCD}	-	
Diode thermal resistance, chip-case,chopper	R_{thJCDC}	≤ 0.125	
Insulation test voltage, $t = 1\text{min.}$	V_{is}	2500	Vac
Creepage distance	-	20	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 8\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	- -	2.5 3.1	3 3.7	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	- -	3 12	4 -	mA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	400	

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 200\text{ A}$	g_{fs}	108	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	13	-	nF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	2	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	1	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\text{ }\Omega$	$t_{d(on)}$	-	110	220	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\text{ }\Omega$	t_r	-	80	160	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\text{ }\Omega$	$t_{d(off)}$	-	550	800	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\text{ }\Omega$	t_f	-	80	120	

Free-Wheel Diode

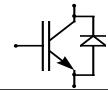
Diode forward voltage $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	-	-	V
		-	-	-	
Reverse recovery time $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	-	-	μs
		-	-	-	
Reverse recovery charge $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rr}	-	-	-	μC
		-	-	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Chopper Diode

Chopper diode forward voltage $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_{FC}	- -	2 1.8	2.5 -	V
Reverse recovery time, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$, $T_j = 25\text{ °C}$	t_{rrC}	-	500	-	ns
Reverse recovery charge, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rrC}	- -	14 40	- -	μC

[illegible]

The circuit diagram shows a 2-to-1 multiplexer implemented using a 74147 decoder and a 7404 inverter. The decoder has two inputs, 1 and 2, and four active-low outputs, 6, 7, 3, and 0. The inverter has one input, 3, and one output, 0. The output of the multiplexer is 0, which is the OR of the decoder outputs 6 and 7. The decoder output 3 is connected to the inverter input 3, and the inverter output 0 is connected to the multiplexer output 0.